

Form PTO 1449 (Modified)		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 247830US-20 CONT		SERIAL NO. 10/762,318 New Cont. App.	
LIST OF REFERENCES CITED BY APPLICANT				APPLICANT Qin-Yi TONG et al.			
				FILING DATE 01-23-2004 Herewith		GROUP 2823 Unassigned	
OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, etc.)							
JAG	FC	Bergman, et al., "Donor-Hydrogen Complexes in Passivated Silicon", Physical Review B, Vol. 37, No. 5, pages 2770-2773, February 15, 1988					
JAG	FD	Mahan, et al., "Characterization of Microvoids in Device-Quality Hydrogenated Amorphous Silicon by Small-Angle X-Ray Scatterin and Infrared Measurements", Physical Review B, Vol. 40, No. 17, pages 12024-12027, December 15, 1989					
JAG	FE	Niwano, et al., "Morphology of Hydrofluoric Acid and Ammonium Fluoride-Treated Silicon Surfaces Studied by Surface Infrared Spectroscopy", J. Appl. Phys., Vol. 71, No. 11, pages 5646-5649, June 1, 1992					
JAG	FF	Borenstein, et al., "Kinetic Model for Hydrogen Reactions in Boron-Doped Silicon", J. Appl. Phys., Vol. 73, No. 6, pages 2751-2754, March 15, 1993					
JAG	FG	Lusson, et al., "Hydrogen Configurations and Stability in Amorphous Sputtered Silicon", J. Appl. Phys., Vol. 81, No. 7, pages 3073-3080, April 1, 1997					
JAG	FH	Pearlton, et al., "Hydrogen in Crystalline Semiconductors", Appl. Phys. A, Vol. 43, pages 153-195, 1987					
JAG	FI	McQuaid, et al., "Passivation, Structural Modification, and Etching of Amorphous Silicon in Hydrogen Plasmas", J. Appl. Phys., Vol. 81, No. 11, pages 7812-7818, June 1, 1997					
JAG	FJ	Bhattacharya, et al., "Transferred Substrate Schottky-Collector Heterojunction Bipolar Transistors: First Results and Scaling Laws for High f_{max} ", IEEE Electron Device Letters, Vol. 16, No. 8, pages 357-359, August 1995					
JAG	FK	Agarwal, et al., "A 277-GHz f_{max} Transferred-Substrate Heterojunction Bipolar Transistor", IEEE Electron Device Letters, Vol. 18, No. 5, pages 228-231, May 1997					
JAG	FL	Lee, et al., "A > 500 GHz f_{max} Transferred-Substrate Heterojunction Bipolar Transistor IC Technology", IEEE Electron Device Letters, Vol. 19, No. 3, pages 77-79, March 1998					
JAG	FM	Lee, et al., "Submicron Transferred-Substrate Heterojunction Bipolar Transistors", IEEE Electron Device Letters, Vol. 20, No. 8, pages 396-398, August 1999					
JAG	FN	Mitani, et al., "A New Evaluation Method of Silicon Wafer Bonding Interfaces and Bonding Strength by KOH Etching", Jpn. J. Applied Phys., Vol. 31, Part 1, No. 4, pages 969-974, April 1992					
JAG	FO	Mitani, et al., "Causes and Prevention of Temperature-Dependent Bubbles in Silicon Wafer Bonding", Jpn. J. Appl. Phys., Vol. 30, No. 4, pages 615-622, April 1991					
JAG	FP	Stengl, et al., "A Model for the Silicon Wafer Bonding Process", Jpn. J. Appl. Phys., Vol. 28, No. 10, pages 1735-1741, October 1989					
JAG	FQ	Lee, et al., "A New Leakage Component Caused by the Interaction of Residual Stress and the Relative Position of Poly-Si Gate at Isolation Edge", IEDM Technical Digest, Vol. 95-683, pages 28.2.1-28.2.4, December 10-13, 1995					
JAG	FR	Sperlings, et al., "Diversity and Interfacial Phenomena in Direct Bonding", Proceedings of the First International Symposium on Semiconductor Wafer Bonding: Science, Technology, and Applications Proceedings, Vol. 92-7, pages 18-32, (no date)					
JAG	FS	Yamahata, et al., "Over-220-GHz f_{max} AND- f_{max} InP/InGaAs Double-Heterojunction Bipolar Transistors with a new Hexagonal-Shaped Emitter", IEEE Gallium Arsenide Integrated Circuit Symposium, Technical Digest 1995, pages 163-166, October 29-November 1, 1995					
Examiner <i>Joanne A. March</i>				Date Considered <i>October 12 2005</i>			
*Examiner: Initial if reference is considered; whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							